

IN THE CLAIMS

Please amend the claims as follows:

1. (Original) A method comprising:
patterning a signal line from a metal material as a terminal conductive layer of an integrated circuit die;
patterning a first protective structure to surround the signal line; and
patterning a second protective structure to surround the first protective structure.
2. (Currently Amended) The method of claim 1, further comprising:
patterning the first protective structure as a continuous structure to enclose the signal line; and
patterning the second protective structure as a continuous structure to enclose the first protective structure.
3. (Original) The method of claim 1, further comprising:
patterning the first and second protective structures to one of a low rail supply line and a high rail supply line.
4. (Currently Amended) A method comprising:
forming a first interconnection metallization layer on a substrate;
forming a second interconnection metallization layer on the first interconnection metallization layer;
forming at least one signal line coupled to the first interconnection metallization layer in the second interconnection metallization;
forming ~~at least one~~ a first protective structure that surrounds the at least one signal line in the second interconnection metallization layer; and
forming a second protective structure that surrounds the first protective structure.
5. (Currently Amended) The method of claim 4, wherein ~~the forming at least one~~ the first protective structure ~~that surrounds the at least one signal line~~ comprises using a continuous loop-like shape protective structure to enclose the signal line; and

wherein forming the second protective structure comprises using a continuous loop-like shape protective structure to enclose the first protective structure .

6. (Currently Amended) The method of claim 4, further comprising coupling ~~the~~ at least one of the protective structures to a low rail supply voltage.

7. (Currently Amended) The method of claim 4, further comprising coupling ~~the~~ at least one of the protective structures to a high rail supply voltage.

8. (Original) The method of claim 4, wherein the ~~at least one~~ first protective structure is spaced from the signal line at approximately 2 microns.

9. (Original) The method of claim 4, wherein the first interconnection metallization layer has a first volume and the second interconnection metallization layer has a second volume greater than the first volume.

10. (Currently Amended) The method of claim 4, wherein the forming ~~at least one~~ the protective structures comprises forming a plurality of protective structures (PSi) for $i = 1 \dots N$, a the first protective structure PS1 surrounding the signal line, each protective structure PSi surrounding a previous protective structure PSi-1.